

Application No. 09/342,235

Art Unit: 2871

Docket No. 0756-1986

Page 2



AMENDED TITLE WITH MARKINGS
TO SHOW CHANGES MADE

[ELECTRO-OPTICAL DEVICE AND METHOD OF DRIVING AND
MANUFACTURING THE SAME]SEMICONDUCTOR DEVICE HAVING AT LEAST
FIRST AND SECOND THIN FILM TRANSISTORS

RECEIVED

JUN 11 2001

TC 2800 MAIL ROOM 1

AMENDED ABSTRACT WTH MARKINGS
TO SHOW CHANGES MADE

--A semiconductor device having a substrate having an insulating surface; at least first and second semiconductor islands formed over the substrate where each of the semiconductor islands has a channel region and a pair of impurity regions; an insulating film formed over the substrate, the insulating film including at least first and second gate insulating films formed over the first and second semiconductor islands, respectively; at least first and second gate electrodes formed over the first and second semiconductor islands with the first and second gate insulating films interposed therebetween; a wiring formed on the insulating film for electrically connecting one of the impurity regions of the first semiconductor island with the second gate electrode where said wiring is connected to the one of the impurity regions through a hold opened in the insulating film; an interlayer insulating film formed over the first and second semiconductor islands, the first and second gate electrodes and the wiring; and a pixel electrode formed over the interlayer insulating film electrically connected to one of the pair of the impurity regions of the second semiconductor island.--